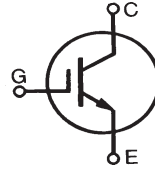


1000V XPT™ GenX4™ IGBT

IXYA24N100A4HV IXYP24N100A4

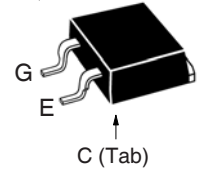
Ultra-Low V_{sat} PT IGBT
for up to 5kHz Switching



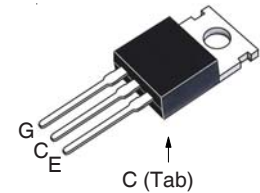
$$\begin{aligned} V_{CES} &= 1000V \\ I_{C110} &= 24A \\ V_{CE(sat)} &\leq 1.9V \\ t_{fi(typ)} &= 125ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	1000	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	1000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	85	A
I_{C110}	$T_C = 110^\circ C$	24	A
I_{CM}	$T_C = 25^\circ C$, 1ms	145	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 48$ $V_{CE} \leq 0.8 \cdot V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 660V$, $T_J = 150^\circ C$ $R_G = 50\Omega$, Non Repetitive	8	μs
P_C	$T_C = 25^\circ C$	375	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
M_d F_C	Mounting Torque (TO-220) Mounting Force (TO-263HV)	1.13/10 10..65 / 22..14.6	Nm/lb.in N/lb
Weight	TO-263HV TO-220	2.5 3.0	g g

TO-263HV
(IXYA..HV)



TO-220
(IXYP)



G = Gate D = Collector
e = Emitter Tab = Collector

Features

- Optimized for Low Conduction Losses
- Positive Thermal Coefficient of V_{ce(sat)}
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1000		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			25 μA 500 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 24A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$		1.65 1.94	V V

Symbol Test Conditions

(T_J = 25°C Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	I _C = 24A, V _{CE} = 10V, Note 1	8	13	S
C_{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		870	pF
C_{oes}			63	pF
C_{res}			36	pF
Q_{g(on)}	I _C = 24A, V _{GE} = 15V, V _{CE} = 0.5 • V _{CES}		44	nC
Q_{ge}			8	nC
Q_{gc}			22	nC
t_{d(on)}	Inductive load, T_J = 25°C I _C = 24A, V _{GE} = 15V V _{CE} = 0.8 • V _{CES} , R _G = 10Ω Note 2		13	ns
t_{ri}			47	ns
E_{on}			3.5	mJ
t_{d(off)}			216	ns
t_{fi}			125	ns
E_{off}			2.3	mJ
t_{d(on)}	Inductive load, T_J = 125°C I _C = 24A, V _{GE} = 15V V _{CE} = 0.8 • V _{CES} , R _G = 10Ω Note 2		13	ns
t_{ri}			40	ns
E_{on}			3.9	mJ
t_{d(off)}			290	ns
t_{fi}			235	ns
E_{off}			3.7	mJ
R_{thJC}	TO-220		0.50	0.40 °C/W
R_{thCS}				°C/W

Notes:

1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

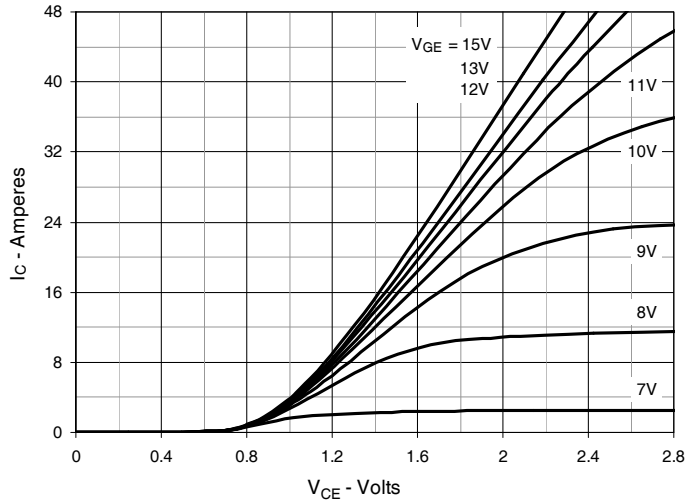
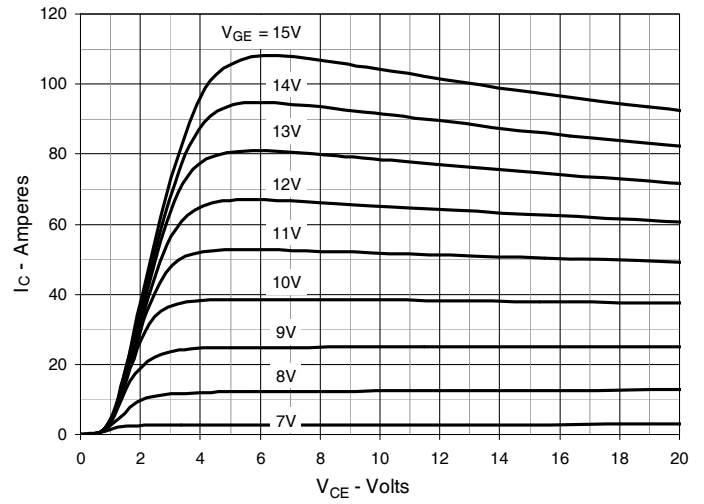
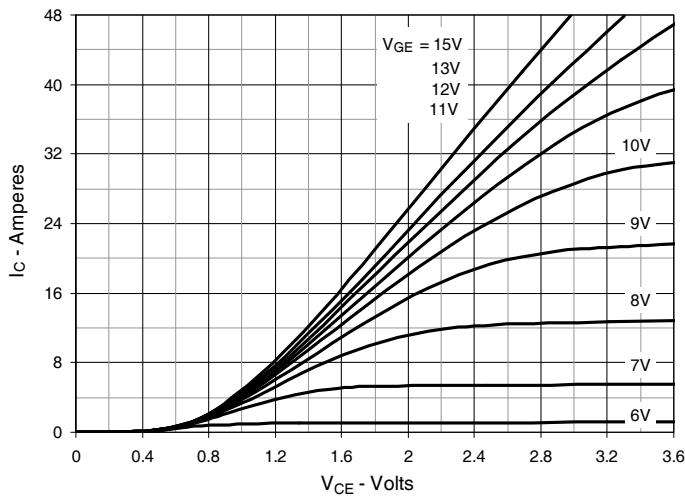
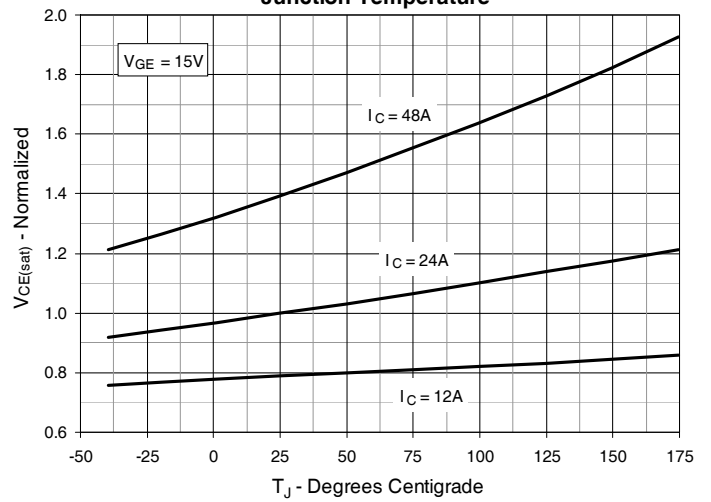
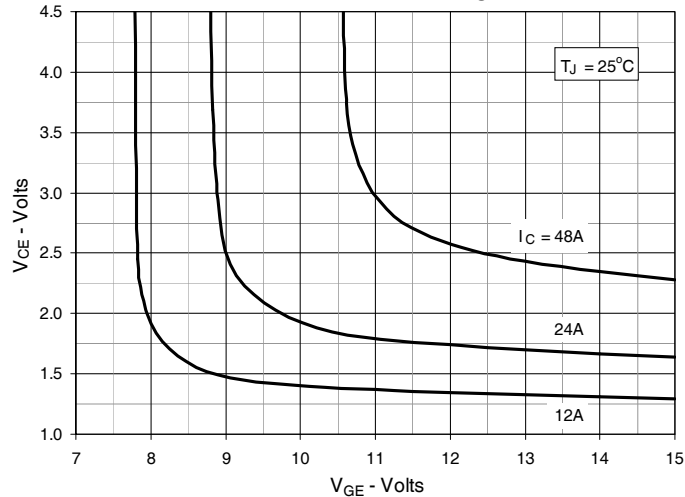
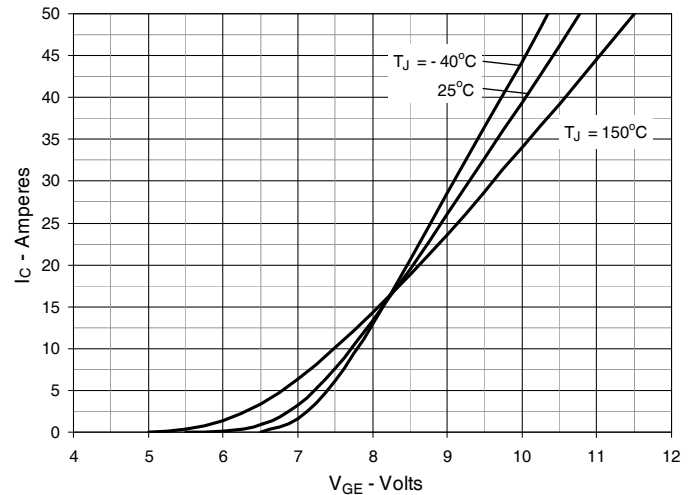
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

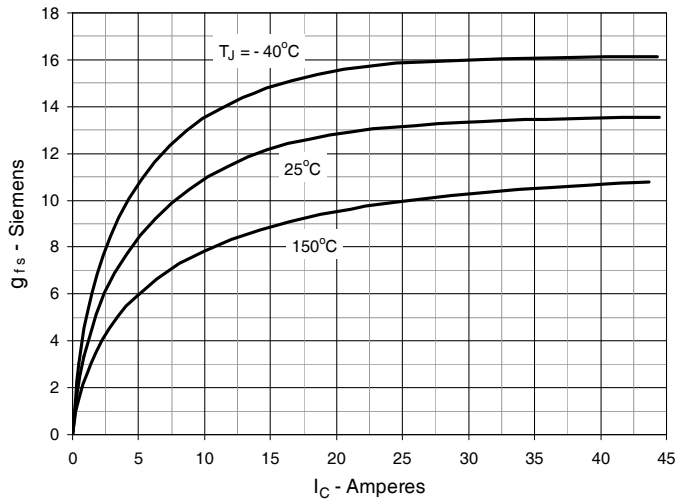


Fig. 8. Gate Charge

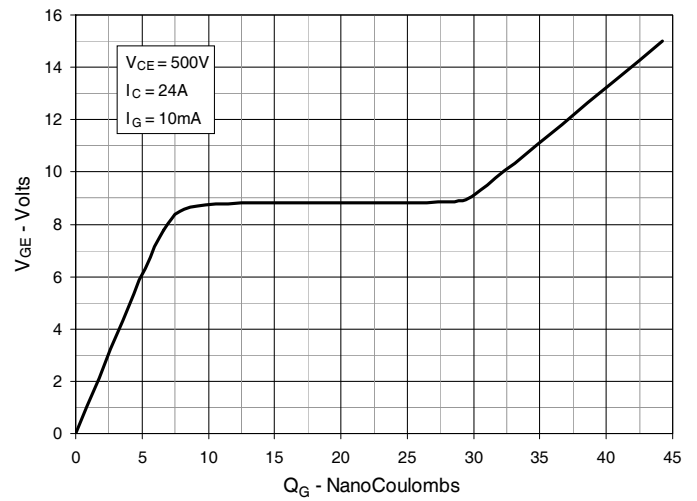


Fig. 9. Capacitance

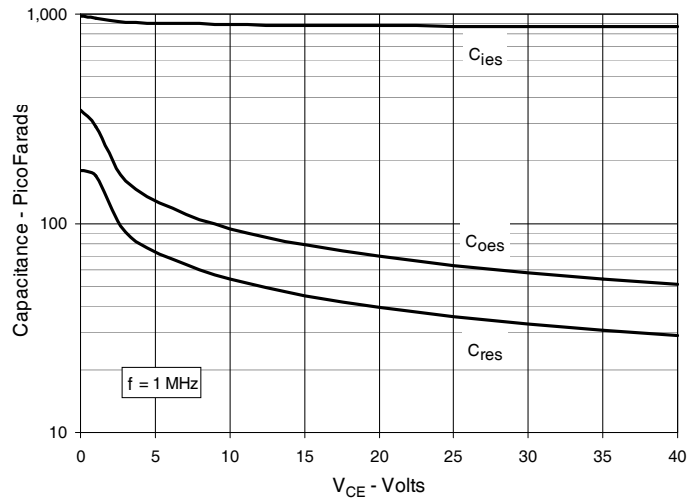


Fig. 10. Reverse-Bias Safe Operating Area

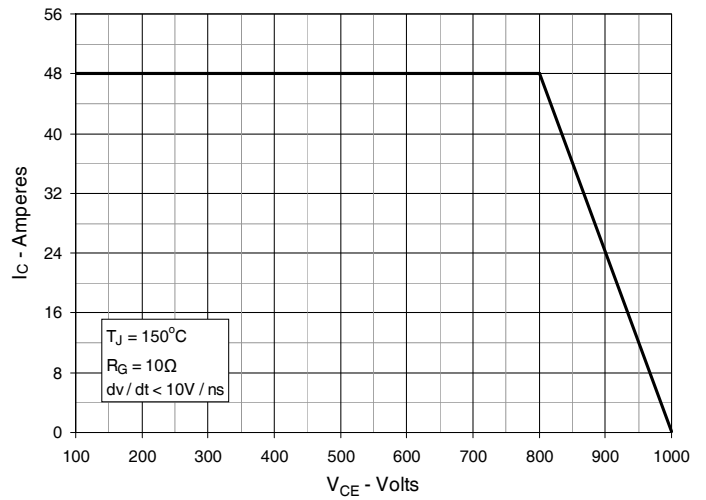


Fig. 11. Maximum Transient Thermal Impedance

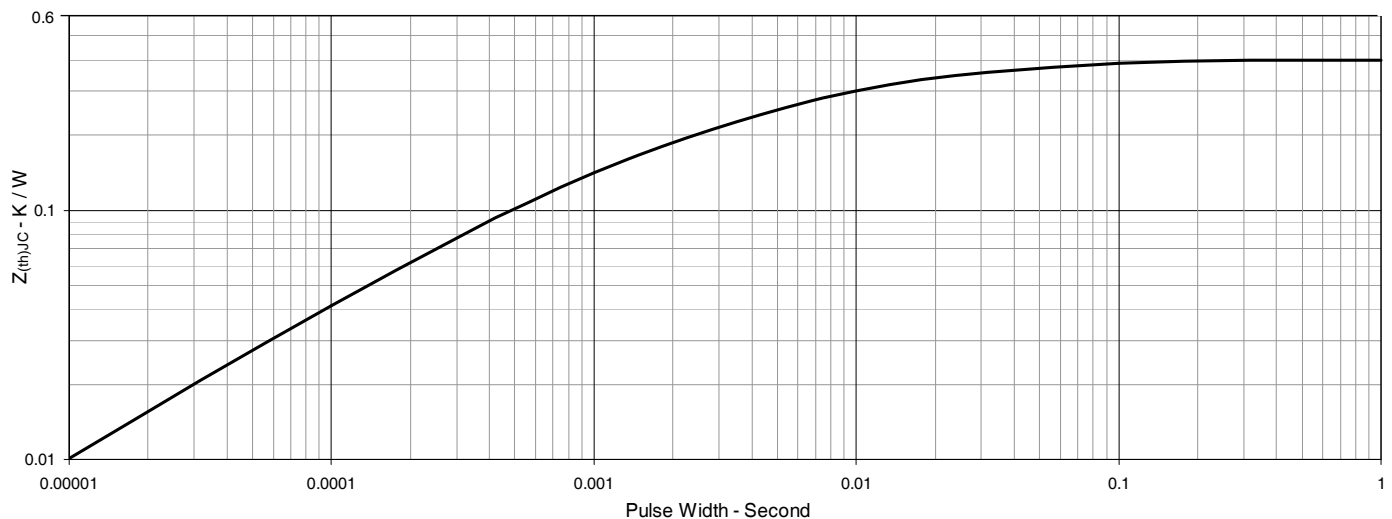


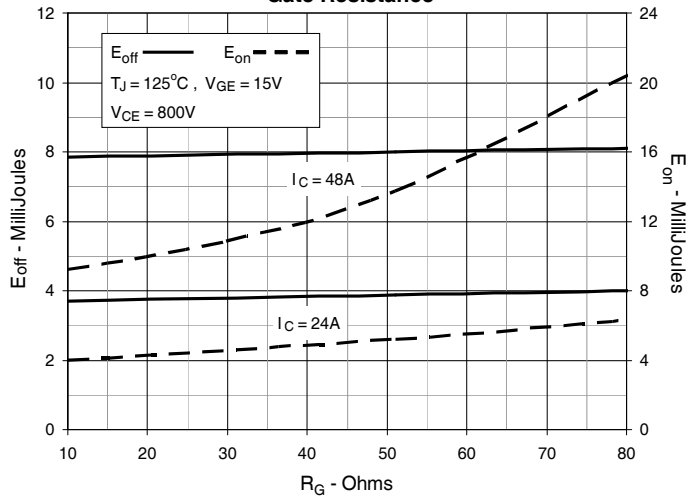
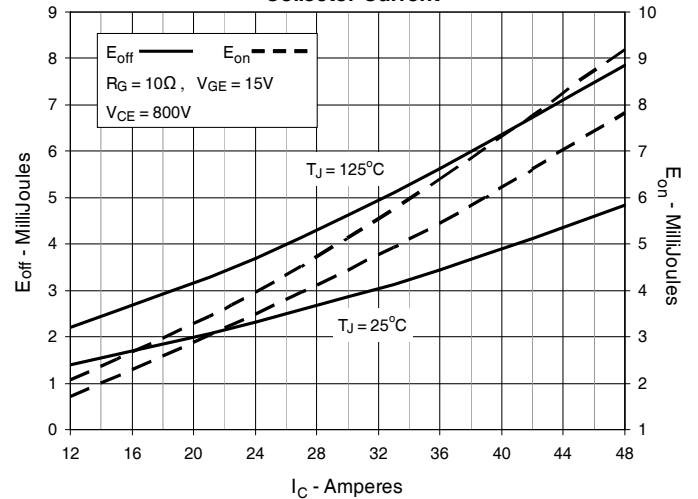
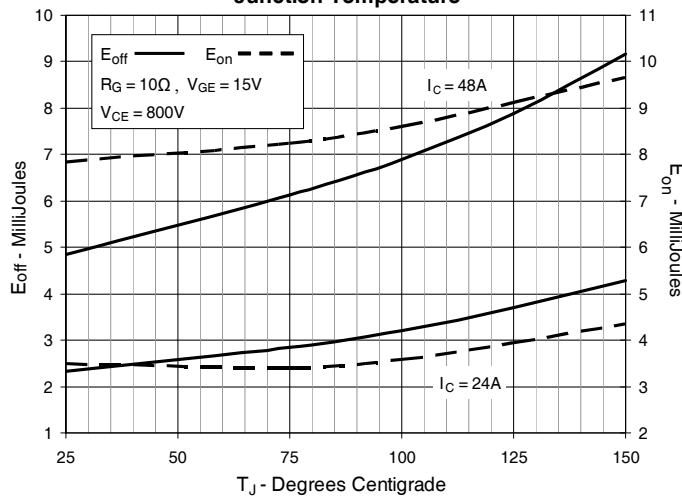
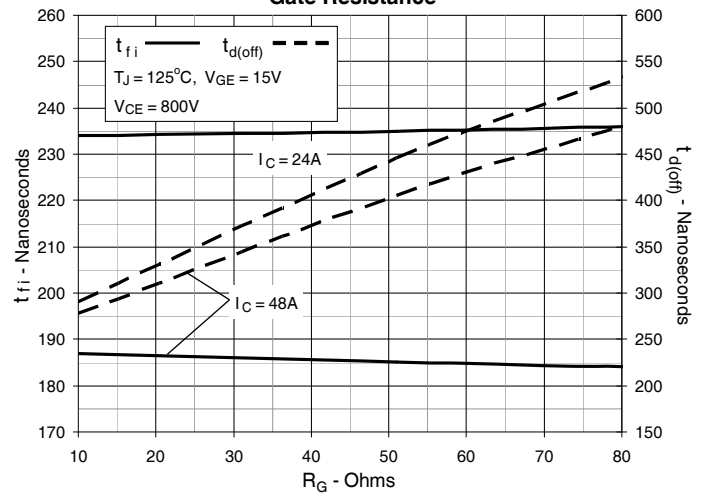
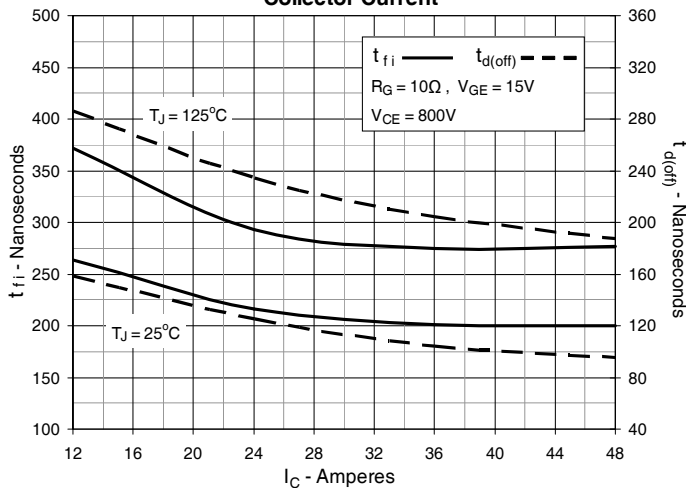
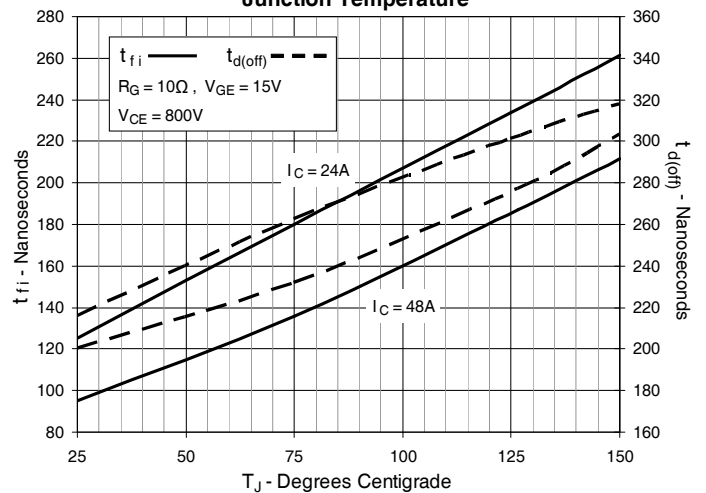
Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 13. Inductive Switching Energy Loss vs. Collector Current

Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

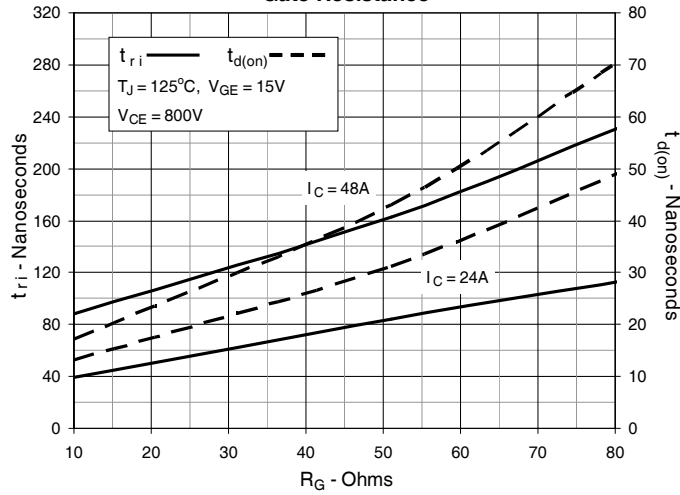


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

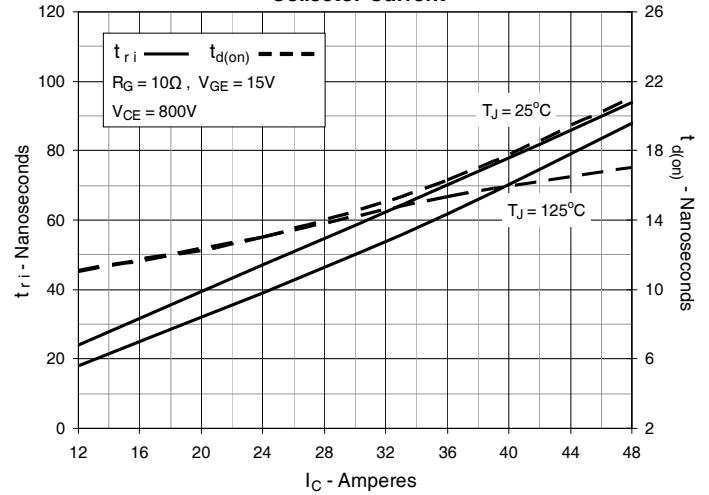
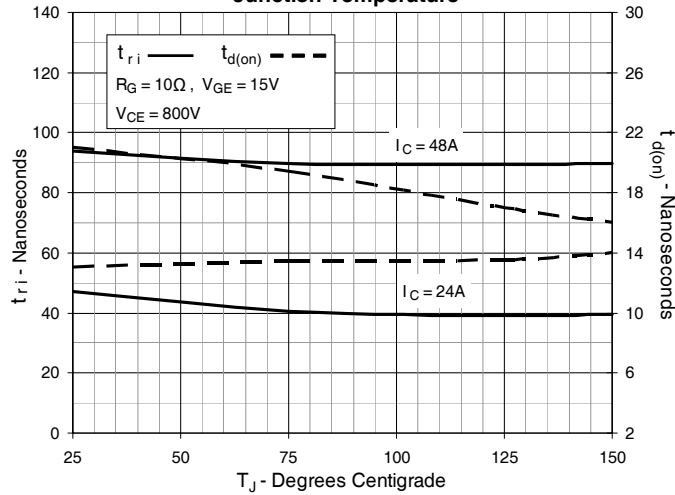
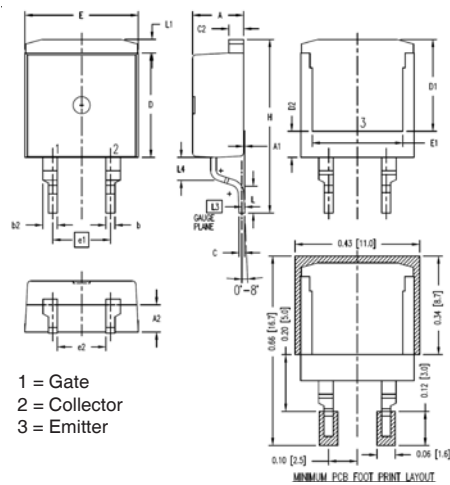
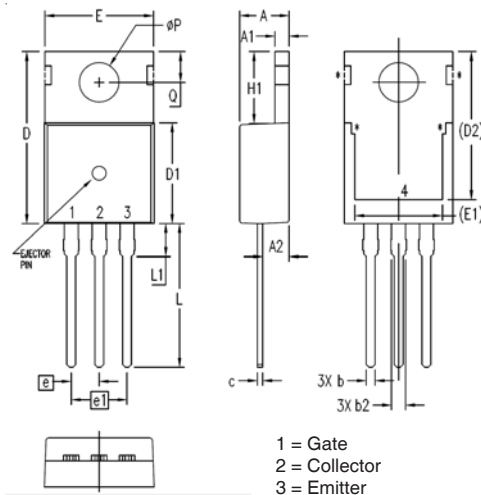


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature



TO-263HV Outline


SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.054	1.18	1.38
C	.018	.024	0.45	0.60
C2	.049	.055	1.25	1.40
D	.354	.370	9.00	9.40
D1	.311	.327	7.90	8.30
D2	.083	.098	2.10	2.50
E	.386	.402	9.80	10.20
E1	.307	.323	7.80	8.20
e1	.200	BSC	5.08	BSC
(e2)	.163	.174	4.13	4.43
H	.591	.614	15.00	15.60
L	.079	.102	2.00	2.60
L1	.039	.055	1.00	1.40
L3	.010	BSC	0.254	BSC
(L4)	.071	.087	1.80	2.20

TO-220 Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100	BSC	2.54	BSC
e1	.200	BSC	5.08	BSC
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
ØP	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20



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